3-D SPIRAL STACKED INDUCTOR ON SEMICONDUCTOR MATERIAL

ABSTRACT

A 3-D spiral stacked inductor is provided having a substrate [112] with a plurality of turns [124, 126, 128] in a plurality of levels [150', 150", 150'"] wherein the number of levels increases from an inner turn to the outer turn of the inductor. First and second connecting portions [130, 134] are respectively connected to an inner turn and an outermost turn, and a dielectric material [116, 121] contains the first and second connecting portions [130, 134] and the plurality of turns [124, 126, 128] over the substrate [112].

(Figure 4)